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FDFS2P106A

Data Sheet

Integrated 60V P-Channel PowerTrench MOSFET and Schottky Diode profile ,MOSFET 60V P-Ch PowerTrench Integrated

Manufacturers	ON Semiconductor, LLC
Package/Case	SO8
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for FDFS2P106A or Email to us: sales@ovaga.com We will contact you in 12 hours.

General Description

The FDFS2P106A combines the exceptional performance of PowerTrench MOSFET technology with a very low forward voltage drop Schottky barrier rectifier in an SO-8 package. This device is designed specifically as a single package solution for DC to DC converters. It features a fast switching, low gate charge MOSFET with very low on-state resistance. The independently connected Schottky diode allows its use in a variety of DC/DC converter topologies.

Features

VF < 0.53 V @ 1 A

VF < 0.45 V @ 1 A>

VF < 0.62 V @ 2 A

Schottky and MOSFET incorporated into singlepower surface mount SO-8 package

Electrically independent Schottky and MOSFETpinout for design flexibility

Application

<u>RFO</u>

ONSEMI



Related Products



FDC645N ON Semiconductor, LLC SSOT-6



FDC6305N ON Semiconductor, LLC

SSOT-6



FDD8647L

ON Semiconductor, LLC TO-252-3



FDD5N50NZTM ON Semiconductor, LLC TO-252



FDC637BNZ

ON Semiconductor, LLC SSOT-6

FDC602P

ON Semiconductor, LLC SOT163

FDB070AN06A0

ON Semiconductor, LLC TO-263

FDD3670

ON Semiconductor, LLC TO-252AA



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